IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
(Case No. 211.001-D3-US)

In the Application of: **Fazan et al.**	)	Group Art Unit:
Serial No: **10/724,648**	)	Before Examiner
Filed: **December 1, 2003**	)	
Title: **Semiconductor Device**	)	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on March 15, 2004
Date
Michiko Sites
(person signing this certificate)
Michiko Sites
Signature

FIRST INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Submitted herewith are twenty-three (23) sheets of a modified Form PTO-1449. The documents listed on the modified Form PTO-1449 were provided or cited during the prosecution of parent applications of the above-captioned application are not enclosed herewith. (See 37 C.F.R. §1.98(d) and MPEP 609). Should the Examiner desire an additional copy of the documents previously provided or cited during the prosecution of parent applications, kindly contact the undersigned.

It is respectfully requested that the Examiner make his/her consideration of these references formally of record with the initial Office Action.

Respectfully submitted,

Date: March 15, 2004

Neil A. Steinberg
Reg. No. 34,735
650-968-8079

PTO-1449 (Modified)	ATTY. DOCKET NO.	SERIAL NUMBER
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	211.001-D3-US	10/724,648
	APPLICANT(S) Fazan et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	FILING DATE December 1, 2003	GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	4,032,947	6/1977	Kesel et al.			
	3,997,799	12/1976	Baker			
	5,448,513	9/1995	Hu et al.			
	4,298,962	11/1981	Hamano et al.			
	3,439,214	4/1969	Kabell			
	6,081,443	6/2000	Morishita			
	6,111,778	8/2000	MacDonald et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	FR 2 197 494	3/1974	French				
	EP 1 180 799	2/2002	European				
	EP 0 030 856	6/1981	European				
	GB 1 414 228	11/1975	Great Britain				
	EP 0 694 977	1/1996	European				
	JP 02 294076	2/1991	Japanese				
	EP 1 237 193	9/2002	European				
	EP 0 878 804	11/1998	European				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"The Multistable Charge-Controlled Memory Effect in SOI MOS Transistors at Low Temperatures", Tack et al., IEEE Transactions on Electron Devices, Vol. 37, No. 5, May 1990, pp.1373-1382

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	5,936,265	8/1999	Koga			
	5,780,906	7/1998	Wu et al.			
	5,144,390	9/1992	Matloubian			
	5,696,718	12/1997	Hartmann			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	EP 0 801 427	10/1997	European				
	EP 0 513 923	11/1992	European				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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U.S. PATENT DOCUMENTS

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	4,298,962	11/1981	Hamano et al.			
	5,489,792	2/1996	Hu et al.			
	5,982,003	11/1999	Hu et al.			
	6,121,077	9/2000	Hu et al.			
	6,300,649	10/2001	Hu et al.			
	6,518,105	2/2003	Yang et al.			
	2002 0070411	6/2002	Vermandel et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	EP 0 731 972	11/2001	European				
	EP 0 362 961 B1	2/1994	European				
	EP 0 362 961 A1	4.1990	European				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"A Capacitorless Double-Gate DRAM Cell", Kuo et al., IEEE Electron Device Letters, Vol. 23, No. 6, June 2002, pp.345-347
	"A Capacitorless Double-Gate DRAM Cell for High Density Applications", Kuo et al., IEEE IEDM, 2002, pp.843-946
	"The Multi-Stable Behaviour of SOI-NMOS Transistors at Low Temperatures", Tack et al., Proc. 1988 SOS/SOI Technology Workshop (Sea Palms Resort, St. Simons Island, GA, Oct. 1988), p.78
	"The Multistable Charge-Controlled Memory Effect in SOI MOS Transistors at Low Temperatures", Tack et al., IEEE Transactions on Electron Devices, Vol. 37, No. 5, May 1990, pp.1373-1382
	"Mechanisums of Charge Modulation in the Floating Body of Triple-Well nMOSFET Capacitor-less DRAMs", Villaret et al., Proceedings of the INFOS 2003, Insulating Films on Semiconductors, 13th Bi-annual Conference, June 18-20, 2003, Barcelona (Spain), (4 pages)

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U.S. PATENT DOCUMENTS

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	2001/0055859	12/2001	Yamada et al.			
	2002/0030214	3/2002	Horiguchi			
	2002/0034855	3/2002	Horiguchi et al.			
	2002/0051378	5/2002	Ohsawa			
	2002/0076880	6/2002	Yamada et al.			
	2002/0098643	7/2002	Kawanaka et al.			
	2002/0110018	8/2002	Ohsawa			
	2002/0114191	8/2002	Iwata et al.			
	2002/0130341	9/2002	Horiguchi et al.			
	2002/0160581	10/2002	Watanabe et al.			
	2003/0003608	1/2003	Arikado et al.			
	2003/0015757	1/2003	Ohsawa			
	2003/0035324	2/2003	Fujita et al.			
	2003/0057487	3/2003	Yamada et al.			
	2003/0057490	3/2003	Nagano et al.			
	2003/0112659	6/2003	Ohsawa			

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U.S. PATENT DOCUMENTS

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	2003/0146488	8/2003	Nagano et al.			
	2003/0151112	8/2003	Yamada et al.			
	6,252,281	6/2001	Yamamoto et al.			
	6,292,424	9/2001	Ohsawa			
	6,351,426	2/2002	Ohsawa			
	6,466,511	10/2002	Fujita et al.			
	6,538,916	3/2003	Ohsawa			
	6,548,848	4/2003	Horiguchi et al.			
	6,567,330	5/2003	Fujita et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	EP 1 191 596	3/2002	European				
	EP 1 233 454	8/2002	European				
	JP 247735	8/2000	Japanese				
	JP 274221	9/2000	Japanese				
	JP 389106	12/2000	Japanese				
	JP 180633	6/2001	Japanese				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"A Memory Using One-Transistor Gain Cell on SOI (FBC) with Performance Suitable for Embedded DRAM's", Ohsawa et al., 2003 Symposium on VLSI Circuits Digest of Technical Papers, June 2003 (4 pages)
	"FBC (Floating Body Cell) for Embedded DRAM on SOI, Inoh et al., 2003 Symposium on VLSI Circuits Digest of Technical Papers, June 2003 (2 pages)
	"Toshiba's DRAM Cell Piggybacks on SOI Wafer", Y. Hara, EE Times, June 2003

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	4,979,014	12/1990	Hieda et al.			
	5,258,635	11/1993	Nitayama et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"Memory Design Using a One-Transistor Gain Cell on SOI", Ohsawa et al., IEEE Journal of Solid-State Circuits, Vol. 37, No. 11, November 2002, pp.1510-1522
	"Opposite Side Floating Gate SOI FLASH Memory Cell", Lin et al., IEEE, March 2000, pp.12-15
	"Advanced TFT SRAM Cell Technology Using a Phase-Shift Lithography", Yamanaka et al., IEEE Transactions on Electron Devices, Vol. 42, No. 7, July 1995, pp.1305-1313
	"Soft-Error Characteristics in Bipolar Memory Cells with Small Critical Charge", Idei et al., IEEE Transactions on Electron Devices, Vol. 38, No. 11, November 1991, pp.2465-2471
	"An SOI 4 Transistors Self-Refresh Ultra-Low-Voltage Memory Cell", Thomas et al., IEEE, March 2003, pp.401-404
	"Design of a SOI Memory Cell", Stanojevic et al., IEEE Proc. 21st International Conference on Microelectronics (MIEL '97), Vol. 1, NIS, Yugoslavis, 14-17 September 1997, pp.297-300
	"Effects of Floating Body on Double Polysilicon Partially Depleted SOI Nonvolatile Memory Cell", Chan et al., IEEE Electron Device Letters, Vol. 24, No. 2, February 2003, pp.75-77
	"MOSFET Design Simplifies DRAM", P. Fazan, EE Times, May 14, 2002 (3 pages)
	"One of Application of SOI Memory Cell – Memory Array", Lončar et al., IEEE Proc. 22nd International Conference on Microelectronics (MIEL 2000), Vol. 2, NIŠ, Serbia, 14-17 May 2000, pp.455-458
	"A SOI Current Memory for Analog Signal Processing at High Temperature", Portmann et al., 1999 IEEE International SOI Conference, Oct. 1999, pp.18-19
	"Chip Level Reliability on SOI Embedded Memory", Kim et al., Proceedings 1998 IEEE International SOI Conference, Oct. 1998, pp.135-139

EXAMINER	DATE CONSIDERED

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	5,886,385	3/1999	Arisumi et al.			
	5,929,479	7/1999	Oyama			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"Analysis of Floating-Body-Induced Leakage Current in 0.15μ m SOI DRAM", Terauchi et al., Proceedings 1996 IEEE International SOI Conference, Oct. 1996, pp.138-139
	"Programming and Erase with Floating-Body for High Density Low Voltage Flash EEPROM Fabricated on SOI Wafers", Chi et al., Proceedings 1995 IEEE International SOI Conference, Oct. 1995, pp.129-130
	"Measurement of Transient Effects in SOI DRAM/SRAM Access Transistors", A. Wei, IEEE Electron Device Letters, Vol. 17, No. 5, May 1996, pp.193-195
	"In-Depth Analysis of Opposite Channel Based Charge Injection in SOI MOSFETs and Related Defect Creation and Annihilation", Sinha et al., Elsevier Science, Microelectronic Engineering 28, 1995, pp.383-386
	"Dynamic Effects in SOI MOSFET's", Giffard et al., IEEE, 1991, pp.160-161
	"A Simple 1-Transistor Capacitor-Less Memory Cell for High Performance Embedded DRAMs", Fazan et al., IEEE 2002 Custom Integrated Circuits Conference, June 2002, pp.99-102
	"A Novel Pattern Transfer Process for Bonded SOI Giga-bit DRAMs", Lee et al., Proceedings 1996 IEEE International SOI Conference, Oct. 1996, pp.114-115
	"An Experimental 2-bit/Cell Storage DRAM for Macrocell or Memory-on-Logic Application", Furuyama et al., IEEE Journal of Solid-State Circuits, Vol. 24, No. 2, April 1989, pp.388-393
	"High-Performance Embedded SOI DRAM Architecture for the Low-Power Supply", Yamauchi et al., IEEE Journal of Solid-State Circuits, Vol. 35, No. 8, August 2000, pp.1169-1178
	"An SOI-DRAM with Wide Operating Voltage Range by CMOS/SIMOX Technology", Suma et al., 1994 IEEE International Solid-State Circuits Conference, pp.138-139
	"A Capacitorless DRAM Cell on SOI Substrate", Wann et al., IEEE IEDM, 1993, pp.635-638

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	6,391,658	5/2002	Gates et al.			

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"The Multistable Charge Controlled Memory Effect in SOI Transistors at Low Temperatures", Tack et al., IEEE Workshop on Low Temperature Electronics, 7-8 Aug. 1989, University of Vermont, Burlington, pp.137-141
	"High-Endurance Ultra-Thin Tunnel Oxide in MONOS Device Structure for Dynamic Memory Application", Wann et al., IEEE Electron Device Letters, Vol. 16, No. 11, November 1995, pp.491-493
	"Hot-Carrier Effects in Thin-Film Fully Depleted SOI MOSFET's", Ma et al., IEEE Electron Device Letters, Vol. 15, No. 6, June 1994, pp.218-220
	"Design Analysis of Thin-Body Silicide Source/Drain Devices", 2001 IEEE International SOI Conference, October 2001, pp.21-22
	"SOI MOSFET on Low Cost SPIMOX Substrate", Iyer et al., IEEE IEDM, September 1998, pp.1001-1004
	"Simulation of Floating Body Effect in SOI Circuits Using BSIM3SOI", Tu et al., Proceedings of Technical Papers (IEEE Cat No. 97TH8303), pp.339-342
	"High-Field Transport of Inversion-Layer Electrons and Holes Including Velocity Overshoot", Assaderaghi et al., IEEE Transactions on Electron Devices, Vol. 44, No. 4, April 1997, pp.664-671
	"Dynamic Threshold-Voltage MOSFET (DTMOS) for Ultra-Low Voltage VLSI", Assaderaghi et al., IEEE Transactions on Electron Devices, Vol. 44, No. 3, March 1997, pp.414-422
	"Hot-Carrier-Induced Degradation in Ultra-Thin-Film Fully-Depleted SOI MOSFETs", Yu et al., Solid-State Electronics, Vol. 39, No. 12, 1996, pp.1791-1794
	"Hot-Carrier Effect in Ultra-Thin-Film (UTF) Fully-Depleted SOI MOSFET's, Yu et al., 54th Annual Device Research Conference Digest (Cat. No. 96TH8193), pp.22-23

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"SOI MOSFET Design for All-Dimensional Scaling with Short Channel, Narrow Width and Ultra-thin Films", Chan et al., IEEE IEDM, 1995, pp.631-634
	"A Novel Silicon-On-Insulator (SOI) MOSFET for Ultra Low Voltage Operation", Assaderaghi et al., 1994 IEEE Symposium on Low Power Electronics, pp.58-59
	"Interface Characterization of Fully-Depleted SOI MOSFET by a Subthreshold I-V Method", Yu et al., Proceedings 1994 IEEE International SOI Conference, Oct. 1994, pp.63-64
	"A Capacitorless Double-Gate DRAM Cell Design for High Density Applications", Kuo et al., IEEE IEDM, Feb. 2002, pp.843-846
	"A Dynamic Threshold Voltage MOSFET (DTMOS) for Ultra-Low Voltage Operation", Assaderaghi et al., IEEE IEDM, 1994, pp.809-812
	"Dynamic Threshold-Voltage MOSFET (DTMOS) for Ultra-Low Voltage VLSI", Assaderaghi et al., IEEE Transactions on Electron Devices, Vol. 44, No. 3, March 1997, pp.414-422
	"A Capacitorless DRAM Cell on SOI Substrate", Wann et al., IEEE IEDM 1993, pp.635-638
	"Studying the Impact of Gate Tunneling on Dynamic Behaviors of Partially-Depleted SOI CMOS Using BSIMPD", Su et al., IEEE Proceedings of the International Symposium on Quality Electronic Design (ISQED '02), April 2002 (5 pages)
	"Characterization of Front and Back Si-SiO_2 Interfaces in Thick- and Thin-Film Silicon-on-Insulator MOS Structures by the Charge-Pumping Technique", Wouters et al., IEEE Transactions on Electron Devices, Vol. 36, No. 9, September 1989, pp.1746-1750
	"An Analytical Model for the Misis Structure in SOI MOS Devices", Tack et al., Solid-State Electronics Vol. 33, No. 3, 1990, pp.357-364

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"A Long Data Retention SOI DRAM with the Body Refresh Function", Tomishima et al., IEICE Trans. Electron., Vol. E80-C, No. 7, July 1997, pp.899-904
	"A Simple 1-Transistor Capacitor-Less Memory Cell for High Performance Embedded DRAMs", Fazan et al., IEEE 2002 Custom Integrated Circuits Conference, June 2002, pp.99-102
	"High-Endurance Ultra-Thin Tunnel Oxide in MONOS Device Structure for Dynamic Memory Application", Wann et al., IEEE Electron Device Letters, Vol. 16, No. 11, November 1995, pp.491-493
	"Capacitor-Less 1-Transistor DRAM", Fazan et al., 2002 IEEE International SOI Conference, Oct. 2002, pp.10-13
	"Memory Design Using a One-Transistor Gain Cell on SOI", Ohsawa et al., IEEE Journal of Solid-State Circuits, Vol. 37, No. 11, November 2002, pp.1510-1522
	"SOI (Silicon-on-Insulator) for High Speed Ultra Large Scale Integration", C. Hu, Jpn. J. Appl. Phys. Vol. 33 (1994) pp.365-369, Part 1, No. 1B, January 1994
	"Source-Bias Dependent Charge Accumulation in P+ -Poly Gate SOI Dynamic Random Access Memory Cell Transistors", Sim et al., Jpn. J. Appl. Phys. Vol. 37 (1998) pp.1260-1263, Part 1, No. 3B, March 1998
	"Suppression of Parasitic Bipolar Action in Ultra-Thin-Film Fully-Depleted CMOS/SIMOX Devices by Ar-Ion Implantation into Source/Drain Regions", Ohno et al., IEEE Transactions on Electron Devices, Vol. 45, No. 5, May 1998, pp.1071-1076

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	"Fully Isolated Lateral Bipolar-MOS Transistors Fabricated in Zone-Melting-Recrystallized Si Films on SiO_2", Tsaur et al., IEEE Electron Device Letters, Vol. EDL-4, No. 8, August 1983, pp.269-271
	"Silicon-On-Insulator Bipolar Transistors", Rodder et al., IEEE Electron Device Letters, Vol. EDL-4, No. 6, June 1983, pp.193-195
	"Characteristics and Three-Dimensional Integration of MOSFET's in Small-Grain LPCVD Polycrystalline Silicon", Malhi et al., IEEE Transactions on Electron Devices, Vol. ED-32, No. 2, February 1985, pp.258-281
	"Triple-Wel nMOSFET Evaluated as a Capacitor-Less DRAM Cell for Nanoscale Low-Cost & High Density Applications", Villaret et al., Handout at Proceedings of 2003 Silicon Nanoelectronics Workshop, June 8-9, 2003, Kyoto, Japan (2 pages)
	"Mechanisms of Charge Modulation in the Floating Body of Triple-Well NMOSFET Capacitor-less DRAMs", Villaret et al., Handout at Proceedings of INFOS 2003, June 18-20, 2003, Barcelona, Spain (2 pages)
	"Embedded DRAM Process Technology", M. Yamawaki, Proceedings of the Symposium on Semiconductors and Integrated Circuits Technology, 1998, Vol. 55, pp.38-43
	"3-Dimensional Simulation of Turn-off Current in Partially Depleted SOI MOSFETs", Ikeda et al., IEIC Technical Report, Institute of Electronics, Information and Communication Engineers, 1998, Vol. 97, No. 557 (SDM97 186-198), pp.27-34

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	EP 1 288 955 A2	3/2003	European				
	EP 1 280 205 A2	1/2003	European				
	EP 1 253 634 A2	10/2002	European				
	EP 1 241 708 A2	9/2002	European				
	EP 1 209 747 A2	5/2002	European				
	EP 1 204 147 A1	5/2002	European				
	EP 1 204 146 A1	5/2002	European				
	EP 1 179 850 A2	2/2002	European				
	EP 1 162 744 A1	12/2001	European				
	EP 1 162 663 A2	12/2001	European				
	EP 1 073 121 A2	1/2001	European				
	EP 0 993 037 A2	4/2000	European				
	EP 0 980 101 A2	2/2000	European				
	EP 0 971 360 A1	1/2000	European				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED
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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	EP 0 951 072 A1	10/1999	European				
	EP 0 933 820 A1	8/1999	European				
	EP 0 924 766 A2	6/1999	European				
	EP 0 920 059 A2	6/1999	European				
	EP 0 869 511 A2	10/1998	European				
	EP 0 860 878 A2	8/1998	European				
	EP 0 858 109 A2	8/1998	European				
	EP 0 844 671 B1	11/2002	European				
	EP 0 836 194 B1	5/2000	European				
	EP 0 788 165 A2	8/1997	European				
	EP 0 744 772 B1	8/2002	European				
	EP 0 739 097 A2	10/1996	European				
	EP 0 731 972 B1	11/2001	European				
	EP 0 727 822 B1	8/1999	European				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	EP 0 727 820 A1	8/1996	European				
	EP 0 726 601 B1	9/2001	European				
	EP 0 725 402 B1	9/2002	European				
	EP 0 689 252 B1	8/2000	European				
	EP 0 682 370 B1	9/2000	European				
	EP 0 642 173 B1	7/1999	European				
	EP 0 642 173 A1	3/1995	European				
	EP 0 606 758 B1	9/2000	European				
	EP 0 601 590 B1	4/2000	European				
	EP 0 599 506 A1	6/1994	European				
	EP 0 599 388 B1	8/2000	European				
	EP 0 579 566 A2	1/1994	European				
	EP 0 564 204 A2	10/1993	European				
	EP 0 537 677 B1	8/1998	European				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	EP 0 510 607 B1	2/1998	European				
	EP 0 465 961 B1	8/1995	European				
	EP 0 366 882 B1	5/1995	European				
	EP 0 362 961 B1	2/1994	European				
	EP 0 359 551 B1	12/1994	European				
	EP 0 354 348 A2	2/1990	European				
	EP 0 350 057 B1	1/1990	European				
	EP 0 333 426 B1	7/1996	European				
	EP 0 300 157 B1	5/1993	European				
	EP 0 253 631 B1	4/1992	European				
	EP 0 245 515 B1	4/1997	European				
	EP 0 207 619 B1	8/1991	European				
	EP 0 202 515 B1	3/1991	European				
	EP 0 175 378 B1	11/1991	European				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	FILING DATE December 1, 2003	GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	2002/0036322	3/2002	Divakauni et al.			
	5,446,299	8/1995	Acovic et al.			
	5,568,356	10/1996	Schwartz			
	5,627,092	5/1997	Alsmeier et al.			
	5,631,186	5/1997	Park et al.			
	5,740,099	4/1998	Tanigawa			
	5,877,978	3/1999	Morishita et al.			
	5,930,648	7/1999	Yang			
	5,939,745	8/1999	Park et al.			
	5,943,258	8/1999	Houston et al.			
	5,968,840	10/1999	Park et al.			
	5,977,578	11/1999	Tang			
	6,018,172	1/2000	Hidada et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	6,297,090	10/2001	Kim			
	6,384,445	5/2002	Hidaka et al.			
	6,590,258	7/2003	Divakauni et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	JP 62 272561	11/1987	Japanese				
	JP 8 274277	10/1996	Japanese				
	JP 9 82912	3/1997	Japanese				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	FILING DATE December 1, 2003	GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	2002/0064913	5/2002	Adkisson et al.			
	2002/0072155	6/2002	Liu et al.			
	2002/0086463	7/2002	Houston et al.			
	2002/0089038	7/2002	Ning			
	2002/0180069	12/2002	Houston			
	2003/0102497	6/2003	Fried et al.			
	2003/0123279	7/2003	Aipperspach et al.			
	4,791,610	12/1988	Takemae			
	5,388,068	2/1995	Ghoshal et al.			
	5,446,299	8/1995	Acovic et al.			
	5,466,625	11/1995	Hsieh et al.			
	5,528,062	6/1996	Hsieh et al.			
	5,593,912	1/1997	Rajeevakumar			
	5,606,188	2/1997	Bronner et al.			

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	FILING DATE December 1, 2003	GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	5,778,243	7/1998	Aipperspach et al.			
	5,784,311	7/1998	Assaderaghi et al.			
	5,811,283	9/1998	Sun			
	5,886,376	3/1999	Acovic et al.			
	5,897,351	4/1999	Forbes			
	5,943,258	8/1999	Houston et al.			
	5,943,581	8/1999	Lu et al.			
	5,960,265	9/1999	Acovic et al.			
	6,096,598	8/2000	Furukawa et al.			
	6,097,056	8/2000	Hsu et al.			
	6,157,216	12/2000	Lattimore et al.			
	6,171,923	1/2001	Chi et al.			
	6,177,300	1/2001	Houston et al.			
	6,177,708	1/2001	Kuang et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	FILING DATE December 1, 2003	GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	6,214,694	4/2001	Leobandung et al.			
	6,225,158	5/2001	Furukawa et al.			
	6,245,613	6/2001	Hsu et al.			
	6,297,090	10/2001	Kim			
	6,320,227	11/2001	Lee et al.			
	6,333,532	12/2001	Davari et al.			
	6,350,653	2/2002	Adkisson et al.			
	6,403,435	6/2002	Kang et al.			
	6,424,011	7/2002	Assaderaghi et al.			
	6,424,016	7/2002	Houston			
	6,429,477	8/2002	Mandelman et al.			
	6,440,872	8/2002	Mandelman et al.			
	6,441,435	8/2002	Chan			
	6,441,436	8/2002	Wu et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	FILING DATE December 1, 2003	GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	6,492,211	12/2002	Divakaruni et al.			
	6,544,837	4/2003	Divakaruni et al.			
	6,549,450	4/2003	Hsu et al.			
	6,552,398	4/2003	Hsu et al.			
	6,556,477	4/2003	Hsu et al.			
	6,566,177	5/2003	Radens et al.			
	6,590,258	7/2003	Divakauni et al.			
	6,590,259	7/2003	Adkisson et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	JP 11 87649	3/1999	Japanese				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	FILING DATE December 1, 2003	GROUP ART UNIT

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	6,650,565	11/2003	Ohsawa			
	6,632,723	10/2003	Watanabe et al.			
	6,621,725	9/2003	Ohsawa			
	6,617,651	9/2003	Ohsawa			
	6,531,754	3/2003	Nagano et al.			
	2002/0036322	3/2002	Divakauni et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	2003-243528	8/2003	Japanese				
	2002-94027	3/2002	Japanese				
	2002-176154	6/2002	Japanese				
	2002-246571	8/2002	Japanese				
	2002-329795	11/2002	Japanese				
	2002-343886	11/2002	Japanese				
	2002-353080	12/2002	Japanese				
	2003-31693	1/2003	Japanese				
	2003-86712	3/2003	Japanese				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	DRAM Design Using the Taper-Isolated Dynamic RAM Cell, Leiss et al., IEEE Transactions on Electron Devices, Vol. ED-29, No. 4, April 1982, pp707-714

EXAMINER	DATE CONSIDERED
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FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
	2003-100641	4/2003	Japanese				
	2003-100900	4/2003	Japanese				
	2003-132682	5/2003	Japanese				
	2003-203967	7/2003	Japanese				
	2003-243528	8/2003	Japanese				
	09046688	2/1997	Japanese				
	JP 8-213624	8/1996	Japanese				
	JP 3-171768	7/1991	Japanese				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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